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MPC8347E PowerQUICC™ II Pro Integrated Host Processor Hardware Specifications

The MPC8347E PowerQUICC™ II Pro is a next generation PowerQUICC II integrated host processor. The MPC8347E contains a PowerPC™ processor core built on Power Architecture™ technology with system logic for networking, storage, and general-purpose embedded applications. For functional characteristics of the processor, refer to the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*.

To locate published errata or updates for this document, refer to the MPC8347E product summary page on our website listed on the back cover of this document or, contact your local Freescale sales office.

NOTE

The information in this document is accurate for revision 1.1 silicon and earlier. For information on revision 3.0 silicon and later versions (for orderable part numbers ending in A or B), see the *MPC8347EA PowerQUICC™ II Pro Integrated Host Processor Hardware Specifications*.

See Section 23.1, "Part Numbers Fully Addressed by This Document," for silicon revision level determination.

Contents

1 Overview

This section provides a high-level overview of the MPC8347E features. Figure 1 shows the major functional units within the MPC8347E.

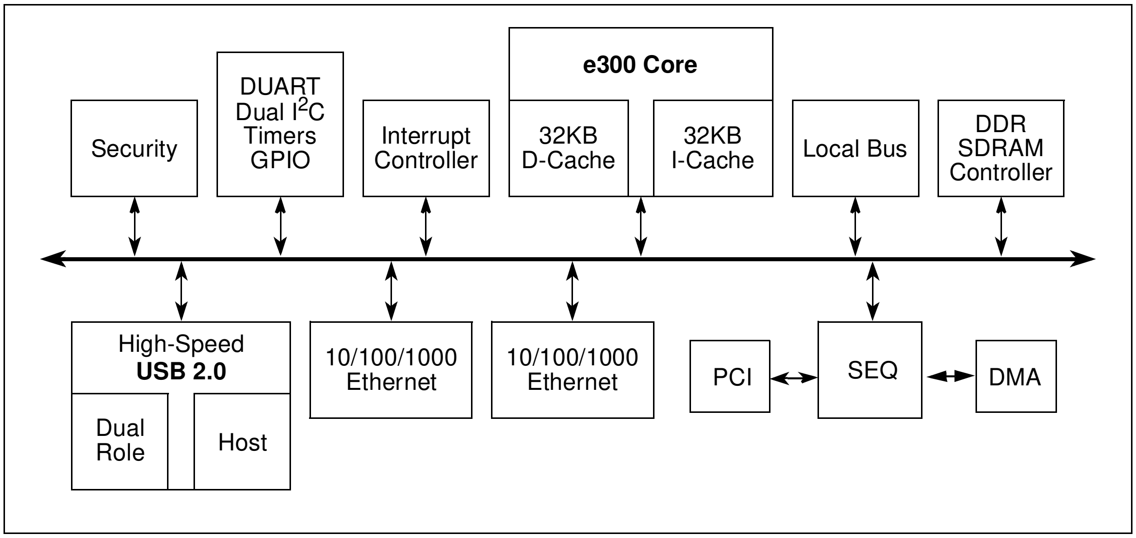


Figure 1. MPC8347E Block Diagram

Major features of the MPC8347E are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
  - High-performance, superscalar processor core
  - Floating-point, integer, load/store, system register, and branch processing units
  - 32-Kbyte instruction cache, 32-Kbyte data cache
  - Lockable portion of L1 cache
  - Dynamic power management
  - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR SDRAM memory controller
  - Programmable timing for DDR-1 SDRAM
  - 32- or 64-bit data interface, up to 333-MHz data rate for TBGA, 266 MHz for PBGA
  - Four banks of memory, each up to 1 Gbyte
  - DRAM chip configurations from 64 Mbit to 1 Gbit with x8/x16 data ports
  - Full error checking and correction (ECC) support
  - Page mode support (up to 16 simultaneous open pages)
  - Contiguous or discontiguous memory mapping
  - Read-modify-write support
  - Sleep mode for self-refresh SDRAM
  - Auto refresh

— On-the-fly power management using CKE
— Registered DIMM support
— 2.5-V SSTL2 compatible I/O

- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
  — Dual controllers designed to comply with IEEE 802.3®, 802.3u®, 820.3x®, 802.3z®, 802.3ac® standards
  — Ethernet physical interfaces:
    – 1000 Mbps IEEE Std. 802.3 GMII/RGMII, IEEE Std. 802.3z TBI/RTBI, full-duplex
    – 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
  — Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
  — 9.6-Kbyte jumbo frame support
  — RMON statistics support
  — Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
  — MII management interface for control and status
  — Programmable CRC generation and checking
- PCI interface
  — Designed to comply with *PCI Specification Revision 2.2*
  — Data bus width:
    – 32-bit data PCI interface operating at up to 66 MHz
  — PCI 3.3-V compatible
  — PCI host bridge capabilities
  — PCI agent mode on PCI interface
  — PCI-to-memory and memory-to-PCI streaming
  — Memory prefetching of PCI read accesses and support for delayed read transactions
  — Posting of processor-to-PCI and PCI-to-memory writes
  — On-chip arbitration supporting five masters on PCI
  — Accesses to all PCI address spaces
  — Parity supported
  — Selectable hardware-enforced coherency
  — Address translation units for address mapping between host and peripheral
  — Dual address cycle for target
  — Internal configuration registers accessible from PCI
- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
  — Public key execution unit (PKEU) :
    – RSA and Diffie-Hellman algorithms

  - Programmable field size up to 2048 bits
  - Elliptic curve cryptography
  - F2m and F(p) modes
  - Programmable field size up to 511 bits
- Data encryption standard (DES) execution unit (DEU)
  - DES and 3DES algorithms
  - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
  - ECB and CBC modes for both DES and 3DES
- Advanced encryption standard unit (AESU)
  - Implements the Rijndael symmetric-key cipher
  - Key lengths of 128, 192, and 256 bits
  - ECB, CBC, CCM, and counter (CTR) modes
- ARC four execution unit (AFEU)
  - Stream cipher compatible with the RC4 algorithm
  - 40- to 128-bit programmable key
- Message digest execution unit (MDEU)
  - SHA with 160- or 256-bit message digest
  - MD5 with 128-bit message digest
  - HMAC with either algorithm
- Random number generator (RNG)
- Four crypto-channels, each supporting multi-command descriptor chains
  - Static and/or dynamic assignment of crypto-execution units through an integrated controller
  - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes

- Universal serial bus (USB) dual role controller
  - USB on-the-go mode with both device and host functionality
  - Complies with USB specification Rev. 2.0
  - Can operate as a stand-alone USB device
    - One upstream facing port
    - Six programmable USB endpoints
  - Can operate as a stand-alone USB host controller
    - USB root hub with one downstream-facing port
    - Enhanced host controller interface (EHCI) compatible
    - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
  - External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)
- Universal serial bus (USB) multi-port host controller
  - Can operate as a stand-alone USB host controller
    - USB root hub with one or two downstream-facing ports

    - Enhanced host controller interface (EHCI) compatible
    - Complies with *USB Specification Rev. 2.0*
  - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
  - Direct connection to a high-speed device without an external hub
  - External PHY with serial and low-pin count (ULPI) interfaces
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Four chip selects support four external slaves
  - Up to eight-beat burst transfers
  - 32-, 16-, and 8-bit port sizes controlled by an on-chip memory controller
  - Three protocol engines on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user-programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
  - Functional and programming compatibility with the MPC8260 interrupt controller
  - Support for 8 external and 35 internal discrete interrupt sources
  - Support for 1 external (optional) and 7 internal machine checkstop interrupt sources
  - Programmable highest priority request
  - Four groups of interrupts with programmable priority
  - External and internal interrupts directed to host processor
  - Redirects interrupts to external $\overline{\text{INTA}}$ pin in core disable mode.
  - Unique vector number for each interrupt source
- Dual industry-standard I^2C interfaces
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
  - System initialization data optionally loaded from I^2C-1 EPROM by boot sequencer embedded hardware
- DMA controller
  - Four independent virtual channels
  - Concurrent execution across multiple channels with programmable bandwidth control
  - All channels accessible to local core and remote PCI masters
  - Misaligned transfer capability

- Data chaining and direct mode
- Interrupt on completed segment and chain

- DUART
  - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
  - 52 parallel I/O pins multiplexed on various chip interfaces
- System timers
  - Periodic interrupt timer
  - Real-time clock
  - Software watchdog timer
  - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1™, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8347E. The MPC8347E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32	V	
PLL supply voltage		AV_{DD}	–0.3 to 1.32	V	
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63	V	
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	

Notes:

1 Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.

2 **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

3 **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

4 **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

5 (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

6 OV_{IN} on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8347E. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

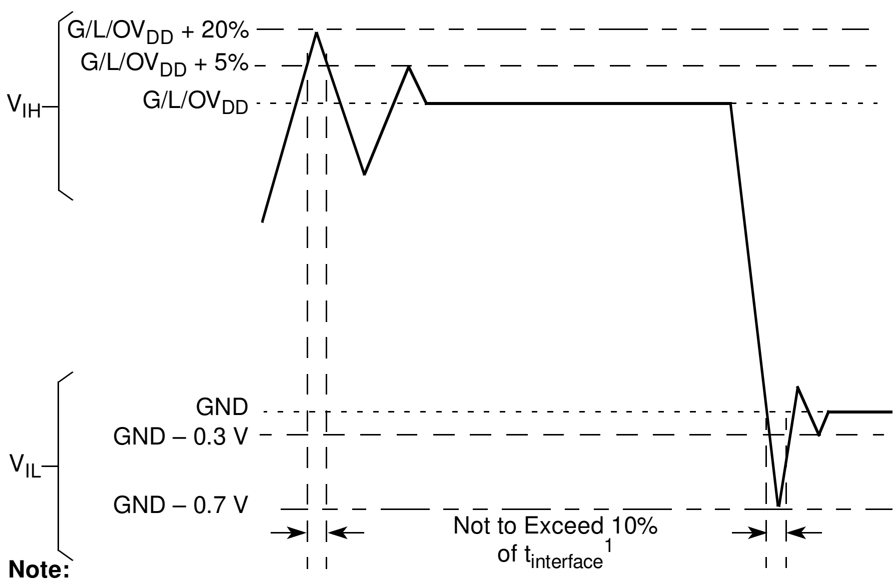
Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV_{DD}	1.2 V ± 60 mV	V	1
DDR DRAM I/O supply voltage	GV_{DD}	2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV_{DD1}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV_{DD2}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	

Note:

1 GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8347E.



Note:

1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8347E for the 3.3-V signals, respectively.

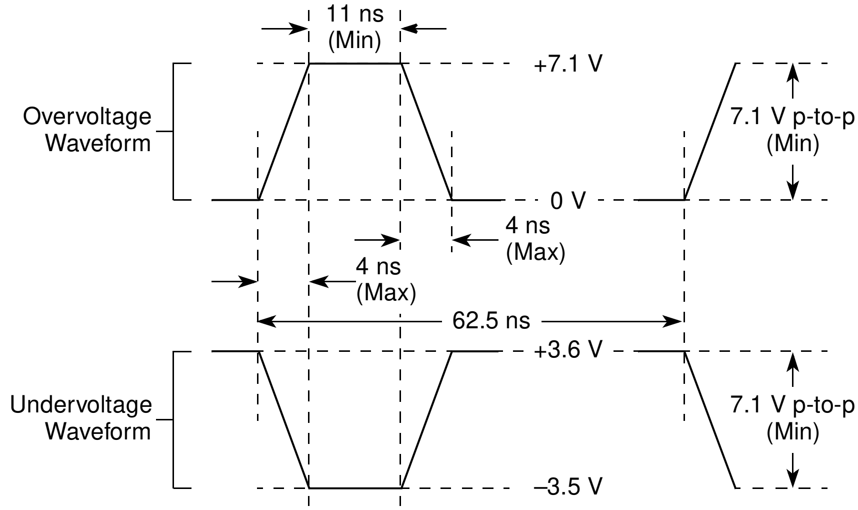


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	OV_{DD} = 3.3 V
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	GV_{DD} = 2.5 V
TSEC/10/100 signals	40	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, JTAG, USB	40	OV_{DD} = 3.3 V
GPIO signals	40	OV_{DD} = 3.3 V, LV_{DD} = 2.5/3.3 V

2.2 Power Sequencing

MPC8347E does not require the core supply voltage and I/O supply voltages to be applied in any particular order. Note that during the power ramp up, before the power supplies are stable, there may be a period of time that I/O pins are actively driven. After the power is stable, as long as $\overline{\text{PORESET}}$ is asserted, most I/O pins are three-stated. To minimize the time that I/O pins are actively driven, it is recommended to apply core voltage before I/O voltage and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up.

3 Power Characteristics

The estimated typical power dissipation for the MPC8347E device is shown in Table 4.

Table 4. MPC8347E Power Dissipation[1]

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T_J = 65	Typical[2,3]	Maximum[4]	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W
TBGA	333	333	2.0	3.0	3.2	W
		166	1.8	2.8	2.9	W
	400	266	2.1	3.0	3.3	W
		133	1.9	2.9	3.1	W
	450	300	2.3	3.2	3.5	W
		150	2.1	3.0	3.2	W
	500	333	2.4	3.3	3.6	W
		166	2.2	3.1	3.4	W
	533	266	2.4	3.3	3.6	W
		133	2.2	3.1	3.4	W

1 The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.
2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8347E.

Table 5. MPC8347E Typical I/O Power Dissipation

Interface	Parameter	DDR2 GV_{DD} (1.8 V)	DDR1 GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	—	0.42	—	—	—	W	—
	200 MHz, 64 bits	—	0.55	—	—	—	W	—
	266 MHz, 32 bits	—	0.5	—	—	—	W	—
	266 MHz, 64 bits	—	0.66	—	—	—	W	—
	300 MHz,[1] 32 bits	—	0.54	—	—	—	W	—
	300 MHz,[1] 64 bits	—	0.7	—	—	—	W	—
	333 MHz,[1] 32 bits	—	0.58	—	—	—	W	—
	333 MHz,[1] 64 bits	—	0.76	—	—	—	W	—
	400 MHz,[1] 32 bits	—	—	—	—	—		—
	400 MHz,[1] 64 bits	—	—	—	—	—		—
PCI I/O load = 30 pF	33 MHz, 32 bits	—	—	0.04	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
Local bus I/O load = 25 pF	167 MHz, 32 bits	—	—	0.34	—	—	W	—
	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O		—	—	0.01	—	—	W	—

1 TBGA package only.

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8347E.

4.1 DC Electrical Characteristics

Table 7 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the MPC8347E.

Table 6. CLKIN DC Timing Specifications

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	0 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±10	µA
PCI_SYNC_IN input current	0 V ≤ V_{IN} ≤ 0.5 V or OV_{DD} – 0.5 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±10	µA
PCI_SYNC_IN input current	0.5 V ≤V_{IN} ≤ OV_{DD} – 0.5 V	I_{IN}	—	±50	µA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8347E can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the MPC8347E.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66	MHz	1, 6
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, USB, security, and TSEC must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.
6. The Spread spectrum clocking. Is allowed with 1% input frequency down-spread at maximum 50KHz modulation rate regardless of input frequency.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8347E.

5.1 RESET DC Electrical Characteristics

Table 8 provides the DC electrical characteristics for the RESET pins of the MPC8347E.

Table 8. RESET Pins DC Electrical Characteristics[1]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}		2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}		–0.3	0.8	V
Input current	I_{IN}			±5	μA
Output high voltage[2]	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:

1. This table applies for pins PORESET, HRESET, SRESET, and QUIESCE.
2. HRESET and SRESET are open drain pins, thus V_{OH} is not relevant for those pins.

5.2 RESET AC Electrical Characteristics

Table 9 provides the reset initialization AC timing specifications of the MPC8347E.

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of HRESET or SRESET (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of PORESET with stable clock applied to CLKIN when the MPC8347E is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of PORESET with stable clock applied to PCI_SYNC_IN when the MPC8347E is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1
HRESET/SRESET assertion (output)	512	—	$t_{PCI\_SYNC\_IN}$	1
HRESET negation to SRESET negation (output)	16	—	$t_{PCI\_SYNC\_IN}$	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8347E is in PCI host mode	4	—	t_{CLKIN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8347E is in PCI agent mode	4	—	$t_{PCI\_SYNC\_IN}$	1

Table 9. RESET Initialization Timing Specifications (continued)

Parameter/Condition	Min	Max	Unit	Notes
Input hold time for POR configuration signals with respect to negation of $\overline{HRESET}$	0	—	ns	
Time for the MPC8347E to turn off POR configuration signals with respect to the assertion of $\overline{HRESET}$	—	4	ns	3
Time for the MPC8347E to turn on POR configuration signals with respect to the negation of $\overline{HRESET}$	1	—	$t_{PCI\_SYNC\_IN}$	1, 3

Notes:

1. $t_{PCI\_SYNC\_IN}$ is the clock period of the input clock applied to PCI_SYNC_IN. In PCI host mode, the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*.
2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is valid only in PCI host mode. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*.
3. POR configuration signals consist of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 10 lists the PLL and DLL lock times.

Table 10. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	µs	
DLL lock times	7680	122,880	csb_clk cycles	1, 2

Notes:

1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The csb_clk is determined by the CLKIN and system PLL ratio. See Section 19, “Clocking.”

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8347E.

NOTE

The information in this document is accurate for revision 1.1 silicon and earlier. For information on revision 3.0 silicon and earlier versions see the *MPC8347EA PowerQUICC™ II Pro Integrated Host Processor Hardware Specifications*. See Section 23.1, “Part Numbers Fully Addressed by This Document,” for silicon revision level determination.

6.1 DDR SDRAM DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8347E.

Table 11. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.18$	V	
Output leakage current	I_{OZ}	–10	10	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	
MV_{REF} input leakage current	I_{VREF}	—	5	μA	

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0\ V \le V_{OUT} \le GV_{DD}$.

Table 12 provides the DDR capacitance.

Table 12. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	
AC input high voltage	V_{IH}	MV_{REF} + 0.31	GV_{DD} + 0.3	V	
MDQS—MDQ/MECC input skew per byte 333 MHz 266 MHz	t_{DISKEW}	—	 750 1125	ps	1

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 <= n <= 7) or ECC (MECC[{0...7}] if n = 8).

Figure 4 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

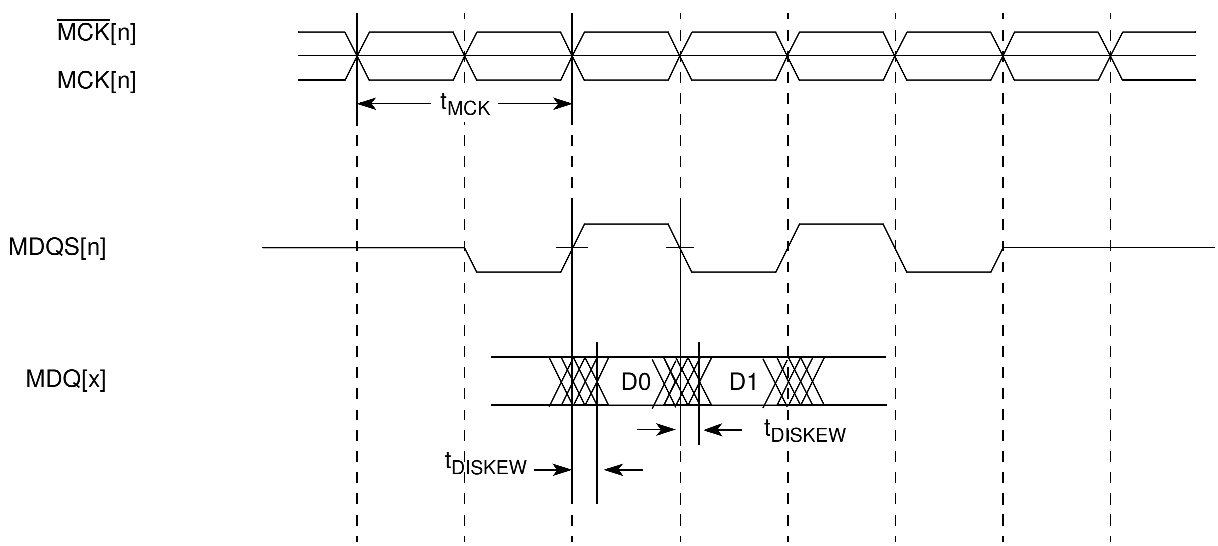


Figure 4. DDR Input Timing Diagram

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t_{AOSKEW}	 –1000 –1100 –1200	 200 300 400	ps	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	 2.8 3.45 4.6	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAX}	 2.0 2.65 3.8	—	ns	4
$\overline{\text{MCS}}$(n) output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	 2.8 3.45 4.6	—	ns	4
$\overline{\text{MCS}}$(n) output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCX}	 2.0 2.65 3.8	—	ns	4
MCK to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHMH}	 –0.9 –1.1 –1.2	 0.3 0.5 0.6	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 900 900 1200	—	ps	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 900 900 1200	—	ps	6
MDQS preamble start	t_{DDKHMP}	$-0.25 \times t_{MCK} - 0.9$	$-0.25 \times t_{MCK} + 0.3$	ns	7

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKLME}	-0.9	0.3	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in 1/4 applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*, for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8347E.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the MPC8347E. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 5 shows the DDR SDRAM output timing for address skew with respect to any MCK.

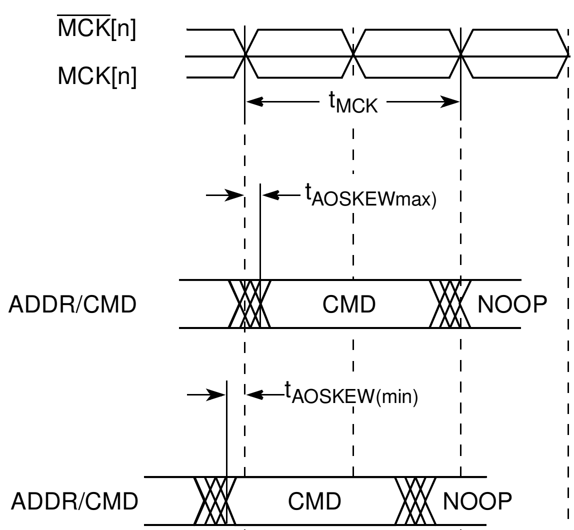


Figure 5. Timing Diagram for t_{AOSKEW} Measurement

Figure 6 provides the AC test load for the DDR bus.

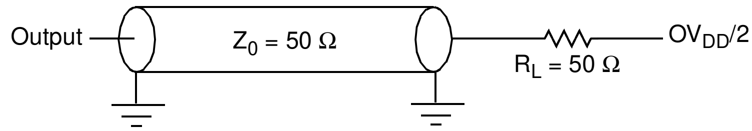


Figure 6. DDR AC Test Load

Table 15 shows the DDR SDRAM measurement conditions.

Table 15. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V_{TH}	MV_{REF} ± 0.31 V	V	1
V_{OUT}	$0.5 \times GV_{DD}$	V	2

Notes:

1. Data input threshold measurement point.
2. Data output measurement point.

Figure 7 shows the DDR SDRAM output timing diagram for source synchronous mode.

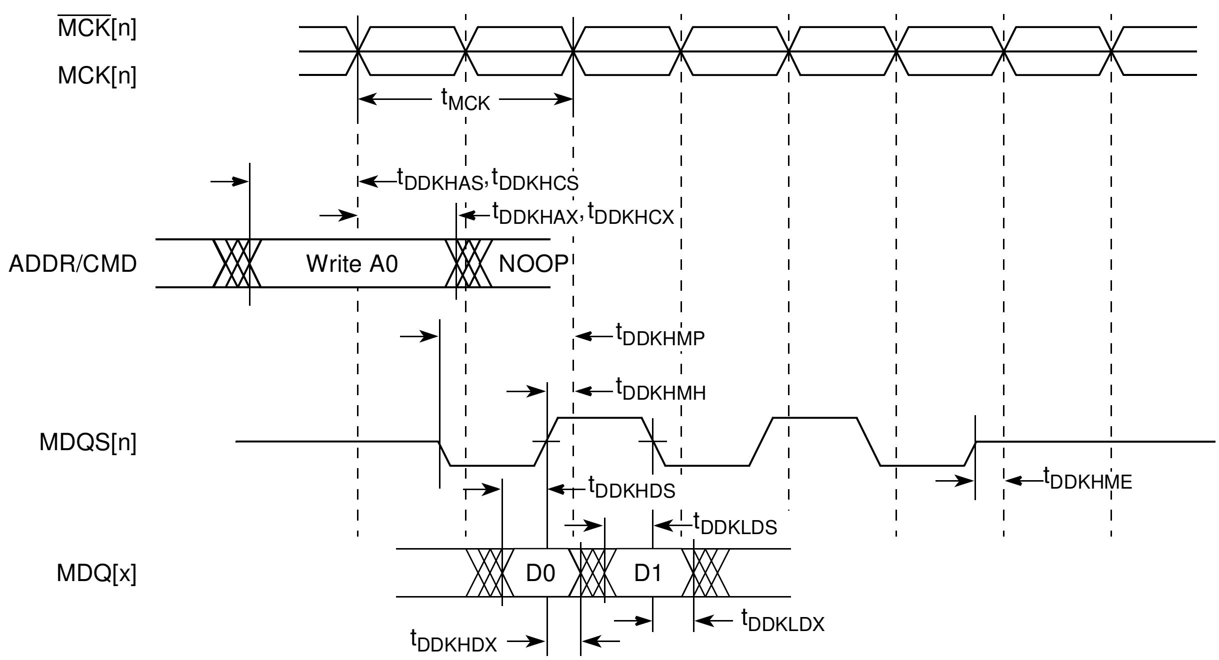


Figure 7. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

Table 16 provides approximate delay information that can be expected for the address and command signals of the DDR controller for various loadings, which can be useful for a system utilizing the DLL. These numbers are the result of simulations for one topology. The delay numbers will strongly depend on the topology used. These delay numbers show the total delay for the address and command to arrive at the DRAM devices. The actual delay could be different than the delays seen in simulation, depending on the system topology. If a heavily loaded system is used, the DLL loop may need to be adjusted to meet setup requirements at the DRAM.

Table 16. Expected Delays for Address/Command

Load	Delay	Unit
4 devices (12 pF)	3.0	ns
9 devices (27 pF)	3.6	ns
36 devices (108 pF) + 40 pF compensation capacitor	5.0	ns
36 devices (108 pF) + 80 pF compensation capacitor	5.2	ns

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8347E.

7.1 DUART DC Electrical Characteristics

Table 17 provides the DC electrical characteristics for the DUART interface of the MPC8347E.

Table 17. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (0.8 V ≤ V_{IN} ≤ 2 V)	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

7.2 DUART AC Electrical Specifications

Table 18 provides the AC timing parameters for the DUART interface of the MPC8347E.

Table 18. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)— GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to the gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 TSEC DC Electrical Characteristics

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 19 and Table 20. The RGMII and RTBI signals in Table 20 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 19. GMII/TBI and MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}[2]	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	40	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–600	—	μA

Notes:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 20. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	μA
Input low current	I_{IL}	V_{IN}[1] = GND		–15	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 21 provides the GMII transmit AC timing specifications.

Table 21. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	43.75	—	56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK clock rise time, V_{IL}(min) to V_{IH}(max)	t_{GTXR}	—	—	1.0	ns
GTX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{GTXF}	—	—	1.0	ns
GTX_CLK125 clock period	t_{G125}[2]	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle measured at LV_{DD}/2	t_{G125H}/t_{G125}	45	—	55	%

Notes:
1. The symbols for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol represents the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Figure 8 shows the GMII transmit AC timing diagram.

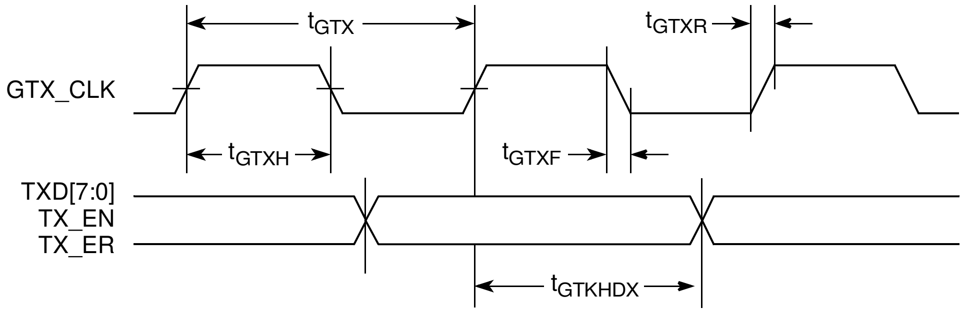


Figure 8. GMII Transmit AC Timing Diagram

8.2.1.2 GMII Receive AC Timing Specifications

Table 22 provides the GMII receive AC timing specifications.

Table 22. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise, V_{IL}(min) to V_{IH}(max)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 9 shows the GMII receive AC timing diagram.

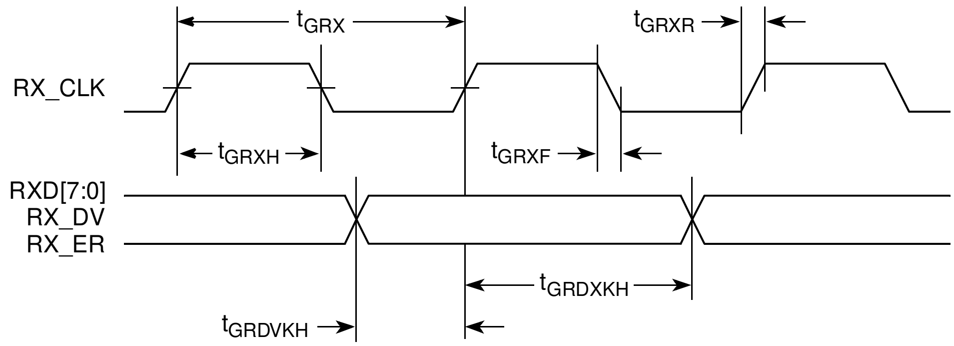


Figure 9. GMII Receive AC Timing Diagram

8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

Table 23 provides the MII transmit AC timing specifications.

Table 23. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).